

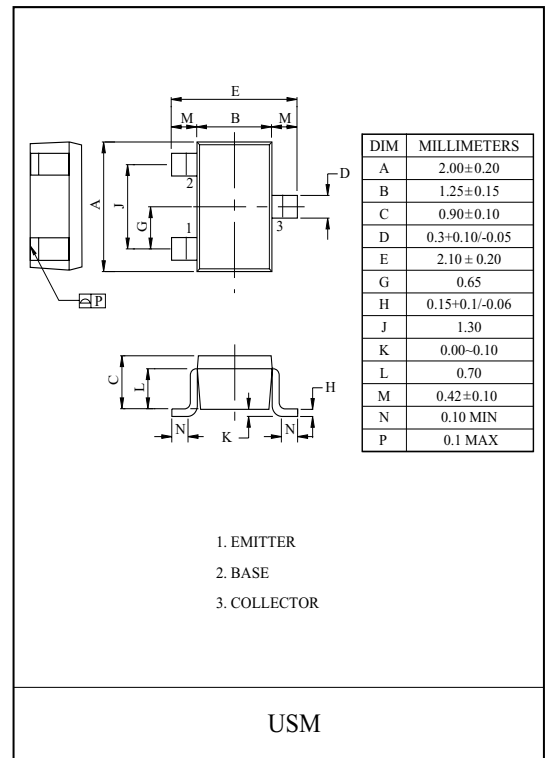
High frequency amplifier transistor, RF switching application.

FEATURES

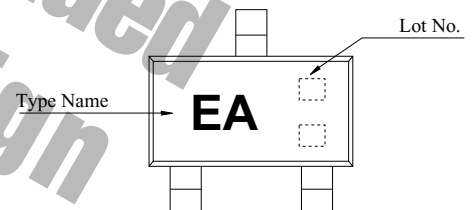
- Very low on resistance (R_{ON}).
- Low capacitance.

MAXIMUM RATING ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	12	V
Collector-Emitter Voltage	V_{CEO}	6	V
Emitter-Base Voltage	V_{EBO}	3	V
Collector Current	I_C	50	mA
Collector Power Dissipation	P_C	100	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	



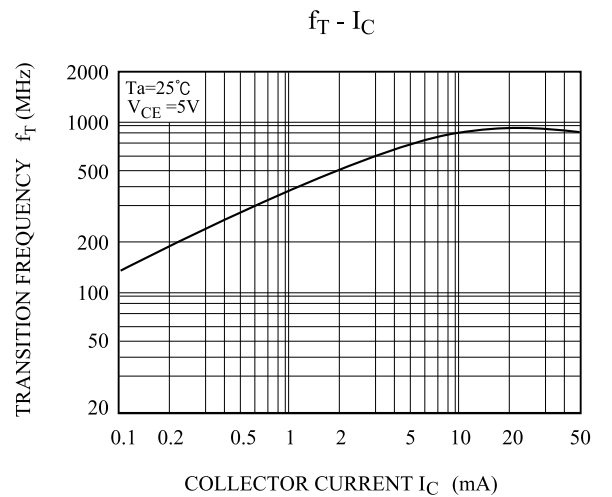
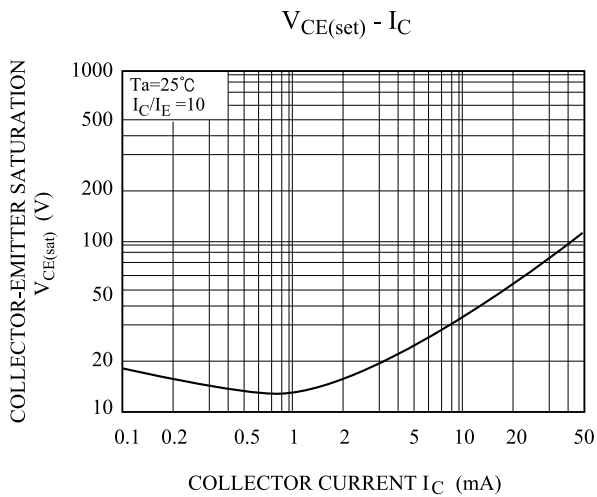
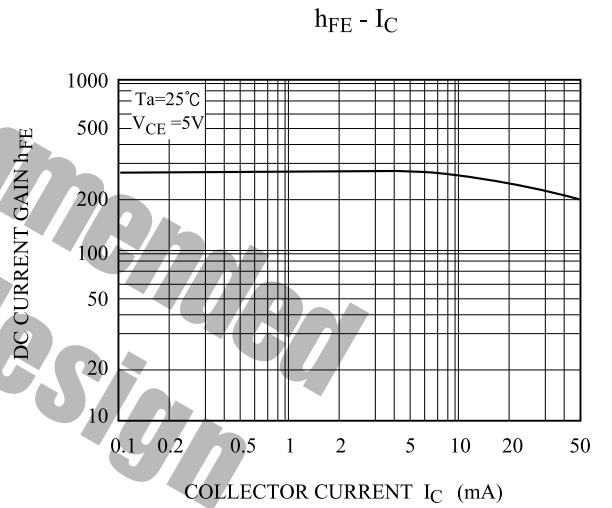
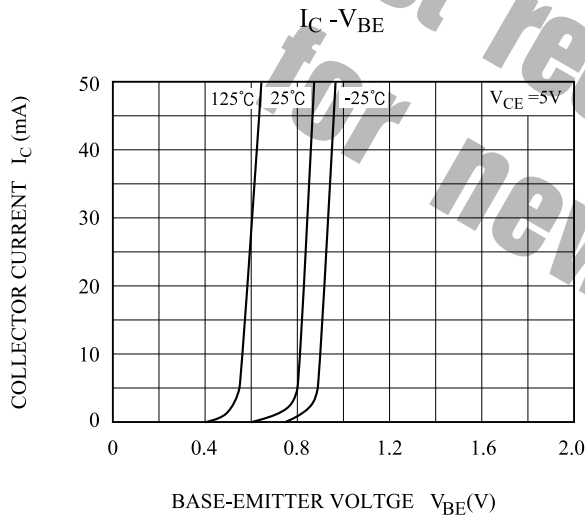
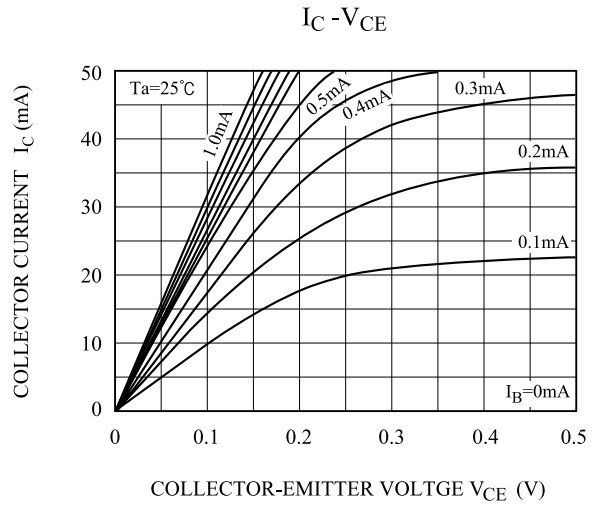
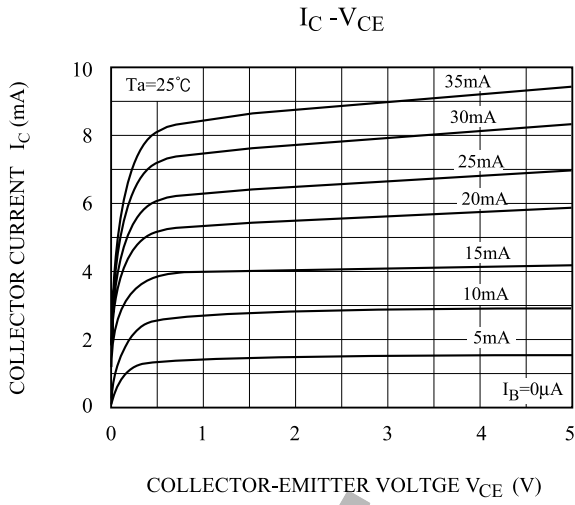
Marking



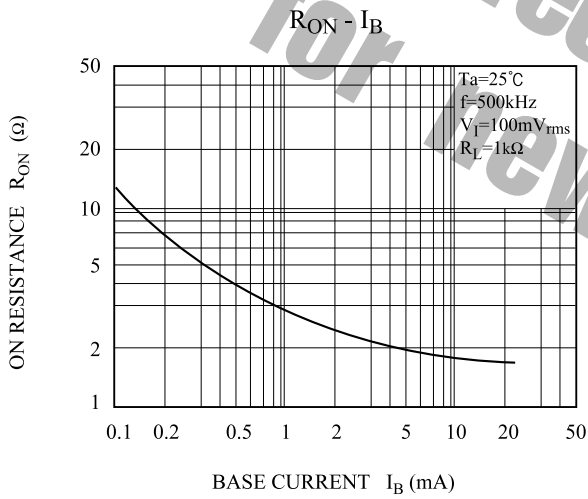
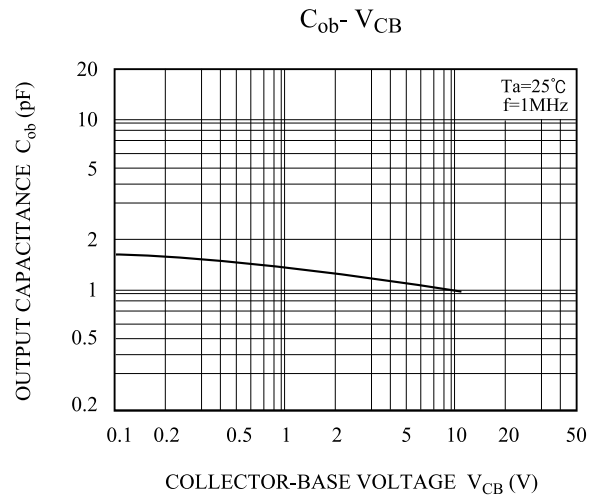
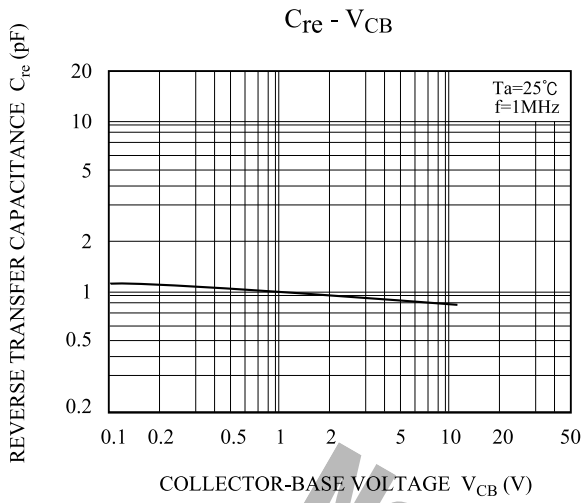
ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB}=10V, I_E=0$	-	-	0.5	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB}=2V, I_C=0$	-	-	0.5	μA
DC Current Gain	h_{FE}	$V_{CE}=5V, I_C=5mA$	270	-	560	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10mA, I_B=1mA$	-	-	0.3	V
Transition Frequency	f_T	$V_{CE}=5V, I_E=-10mA, f=200MHz$	300	800	-	MHz
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0A, f=1MHz$	-	1	1.7	pF
On Resistance	R_{on}	$I_B=3mA, V_I=100mV_{rms}, f=500kHz$	-	2	-	

KTC3708U



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Not recommended for new design